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(54) Title: MINIMIZING TIN OXIDE CHAMBER CLEAN TIME

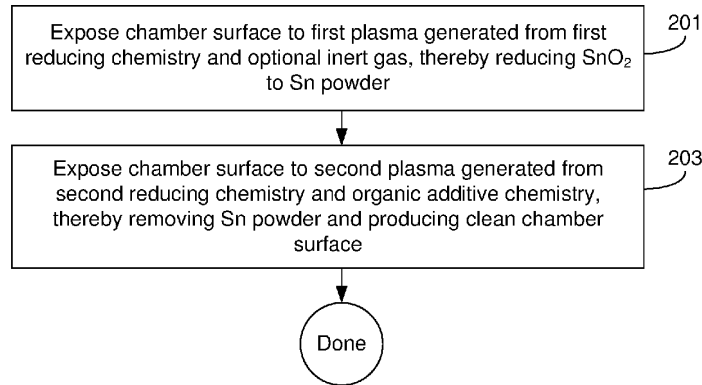


FIG. 2A

(57) Abstract: Techniques described herein relate to methods and apparatus for minimizing tin oxide chamber clean time. In many cases, the chamber is a deposition chamber used for depositing tin oxide on semiconductor substrates. The techniques involve exposing the chamber surface to a first plasma generated from a first plasma generation gas including reducing chemistry to reduce the tin oxide to tin, and then exposing the chamber surface to a second plasma generated from a second plasma generation gas including reducing chemistry and organic additive chemistry to remove the tin from the chamber surface. In some cases, the first plasma used to reduce the tin oxide to tin further includes inert gas.

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